

Vorläufig
preliminary

Elektrische Eigenschaften / electrical properties

Höchstzulässige Werte / maximum rated values

Diode Gleichrichter/ diode rectifier

Periodische Rückw. Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	800	V
Durchlaßstrom Grenzeffektivwert pro Chip RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	I_{FRMSM}	58	A
Gleichrichter Ausgang Grenzeffektivstrom maximum RMS current at Rectifier output	$T_C = 80^{\circ}\text{C}$	I_{RMSmax}	50	A
Stoßstrom Grenzwert surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	448	A
			358	A
Grenzlastintegral I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	1000	A^2s
			642	A^2s

Transistor Wechselrichter/ transistor inverter

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	600	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 65^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C,nom.}$ I_C	15	A
			19	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 65^{\circ}\text{C}$	I_{CRM}	30	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	60	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Wechselrichter/ diode inverter

Dauergleichstrom DC forward current		I_F	15	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	30	A
Grenzlastintegral I^2t - value	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^{\circ}\text{C}$	I^2t	25	A^2s

Transistor Brems-Chopper/ transistor brake-chopper

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	600	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 65^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C,nom.}$ I_C	15	A
			19	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 65^{\circ}\text{C}$	I_{CRM}	30	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	P_{tot}	60	W
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Diode Brems-Chopper/ diode brake-chopper

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Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	30	A

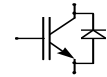
prepared by: Thomas Passe	date of publication: 2003-03-26
approved by: R. Keggenhoff	revision: 2.1

Technische Information / technical information

IGBT-Module
IGBT-Modules

FB15R06KL4B1

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Modul Isolation/ module isolation

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min. NTC connected to Baseplate	V_{ISOL}	2,5	kV
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Elektrische Eigenschaften / electrical properties

Charakteristische Werte / characteristic values

Diode Gleichrichter/ diode rectifier

			min.	typ.	max.	
Durchlaßspannung forward voltage	$T_{vj} = 150^{\circ}\text{C}$, $I_F = 15\text{ A}$	V_F	-	0,8	-	V
Schleusenspannung threshold voltage	$T_{vj} = 150^{\circ}\text{C}$	$V_{(TO)}$	-	0,61	-	V
Ersatzwiderstand slope resistance	$T_{vj} = 150^{\circ}\text{C}$	r_T	-	11	-	mΩ
Sperrstrom reverse current	$T_{vj} = 150^{\circ}\text{C}$, $V_R = 800\text{ V}$	I_R	-	5	-	mA
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	$T_C = 25^{\circ}\text{C}$	R_{AA+CC}	-	11	-	mΩ

Transistor Wechselrichter/ transistor inverter

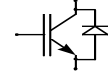
			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$V_{GE} = 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $I_C = 15\text{ A}$	$V_{CE\text{ sat}}$	-	1,95	2,55	V
	$V_{GE} = 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $I_C = 15\text{ A}$		-	2,2	-	V
Gate-Schwellenspannung gate threshold voltage	$V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$, $I_C = 0,4\text{mA}$	$V_{GE(TO)}$	4,5	5,5	6,5	V
Eingangskapazität input capacitance	f = 1MHz, $T_{vj} = 25^{\circ}\text{C}$ $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{res}	-	0,8	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{GE} = 0\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 600\text{V}$	I_{CES}	-	-	5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}	-	-	400	nA
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	$t_{d,on}$	-	37	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	t_r	-	37	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	$t_{d,off}$	-	216	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	t_f	-	17	-	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$ $V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$ $L_S = 80\text{ nH}$	E_{on}	-	0,6	-	mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$ $V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 68\text{ Ohm}$ $L_S = 80\text{ nH}$	E_{off}	-	0,4	-	mJ
Kurzschlußverhalten SC Data	$t_P \leq 10\mu\text{s}$, $V_{GE} \leq 15\text{V}$, $R_G = 68\text{ Ohm}$ $T_{vj} \leq 125^{\circ}\text{C}$, $V_{CC} = 360\text{ V}$ $di/dt = 1000\text{ A}/\mu\text{s}$	I_{SC}	-	60	-	A

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Charakteristische Werte / characteristic values

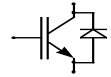
				min.	typ.	max.	
Modulinduktivität stray inductance module		L_{GCE}	-	-	40	nH	
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	$T_C = 25^\circ\text{C}$	R_{CC+EE}	-	10	-	mΩ	
				min.	typ.	max.	
Diode Wechselrichter/ diode inverter							
Durchlaßspannung forward voltage	$V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}, I_F = 15\text{A}$ $V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}, I_F = 15\text{A}$	V_F	-	1,75	2,15	V	
Rückstromspitze peak reverse recovery current	$I_F = I_{Nenn}, -di_F/dt = 600\text{A/us}$ $V_{GE} = -10\text{V}, T_{vj} = 25^\circ\text{C}, V_R = 300\text{V}$ $V_{GE} = -10\text{V}, T_{vj} = 125^\circ\text{C}, V_R = 300\text{V}$	I_{RM}	-	13	-	A	
Sperrverzögerungsladung recovered charge	$I_F = I_{Nenn}, -di_F/dt = 600\text{A/us}$ $V_{GE} = -10\text{V}, T_{vj} = 25^\circ\text{C}, V_R = 300\text{V}$ $V_{GE} = -10\text{V}, T_{vj} = 125^\circ\text{C}, V_R = 300\text{V}$	Q_r	-	0,8	-	μAs	
Abschaltenergie pro Puls reverse recovery energy	$I_F = I_{Nenn}, -di_F/dt = 600\text{A/us}$ $V_{GE} = -10\text{V}, T_{vj} = 25^\circ\text{C}, V_R = 300\text{V}$ $V_{GE} = -10\text{V}, T_{vj} = 125^\circ\text{C}, V_R = 300\text{V}$	E_{rec}	-	0,14	-	mJ	
				min.	typ.	max.	
Transistor Brems-Chopper/ transistor brake-chopper							
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}, I_C = 15,0\text{A}$ $V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}, I_C = 15,0\text{A}$	$V_{CE\text{ sat}}$	-	1,95	2,55	V	
Gate-Schwellenspannung gate threshold voltage	$V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}, I_C = 0,4\text{mA}$	$V_{GE(To)}$	4,5	5,5	6,5	V	
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}$ $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	C_{ies}	-	0,8	-	nF	
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}, V_{CE} = 600\text{V}$		-	-	5,0	mA	
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	I_{GES}	-	-	400	nA	
				min.	typ.	max.	
Diode Brems-Chopper/ diode brake-chopper							
Durchlaßspannung forward voltage	$T_{vj} = 25^\circ\text{C}, I_F = 15\text{A}$ $T_{vj} = 125^\circ\text{C}, I_F = 15\text{A}$	V_F	-	2,15	2,6	V	
				min.	typ.	max.	
NTC-Widerstand/ NTC-thermistor							
Nennwiderstand rated resistance	$T_C = 25^\circ\text{C}$	R_{25}	-	5	-	kΩ	
Abweichung von R_{100} deviation of R_{100}	$T_C = 100^\circ\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%	
Verlustleistung power dissipation	$T_C = 25^\circ\text{C}$	P_{25}			20	mW	
B-Wert B-value	$R_2 = R_1 \exp [B(1/T_2 - 1/T_1)]$	$B_{25/50}$		3375		K	

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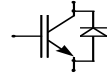
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Thermische Eigenschaften / thermal properties

			min.	typ.	max.		
Innerer Wärmewiderstand thermal resistance, junction to heatsink	Gleichr. Diode/ rectif. diode	$\lambda_{\text{Paste}}=1\text{W/m}^2\text{K}$	R_{thJH}	-	1,1	-	K/W
	Trans. Wechselr./ trans. inverter	$\lambda_{\text{grease}}=1\text{W/m}^2\text{K}$		-	2,4	-	K/W
	Diode Wechselr./ diode inverter			-	4,0	-	K/W
	Trans. Bremse/ trans. brake			-	2,4	-	K/W
	Diode Bremse/ diode brake			-	4,3	-	K/W
Innerer Wärmewiderstand thermal resistance, junction to case	Gleichr. Diode/ rectif. diode		R_{thJC}	-	-	1	K/W
	Trans. Wechselr./ trans. inverter			-	-	2	K/W
	Diode Wechselr./ diode inverter			-	-	2,9	K/W
	Trans. Bremse/ trans. brake			-	-	2	K/W
	Diode Bremse/ diode brake			-	-	3,1	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	Gleichr. Diode/ rectif. diode	$\lambda_{\text{Paste}}=1\text{W/m}^2\text{K}$	R_{thCH}	-	0,2	-	K/W
	Trans. Wechselr./ trans. inverter	$\lambda_{\text{grease}}=1\text{W/m}^2\text{K}$		-	0,6	-	K/W
	Diode Wechselr./ diode inverter			-	1,4	-	K/W
	Trans. Bremse/ trans. brake			-	0,6	-	K/W
	Diode Bremse/ diode brake			-	1,5	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature			T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature			T_{op}	-40	-	125	°C
Lagertemperatur storage temperature			T_{stg}	-40	-	125	°C

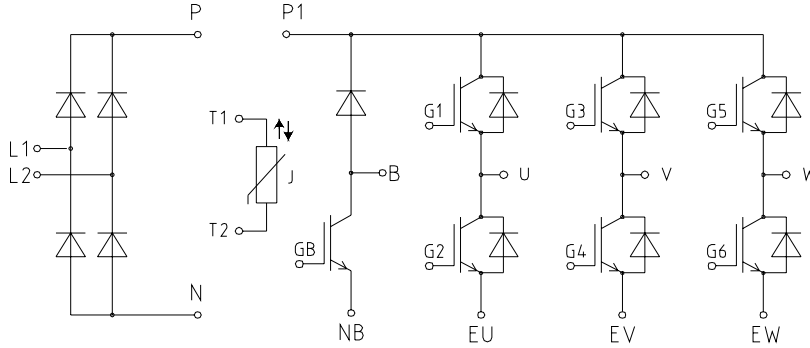
Mechanische Eigenschaften / mechanical properties

Innere Isolation internal insulation				Al_2O_3	
CTI comperative tracking index				225	
Anpreßkraft f. mech. Befestigung pro Feder mounting force per clamp			F	40...80	N
Gewicht weight			G	36	g
Kontakt - Kühlkörper terminal to heatsink	Kriechstrecke creepage distance			13,5	mm
	Luftstrecke clearance distance			12	mm
Terminal - Terminal terminal to terminal	Kriechstrecke creepage distance			7,5	mm
	Luftstrecke clearance distance			7,5	mm



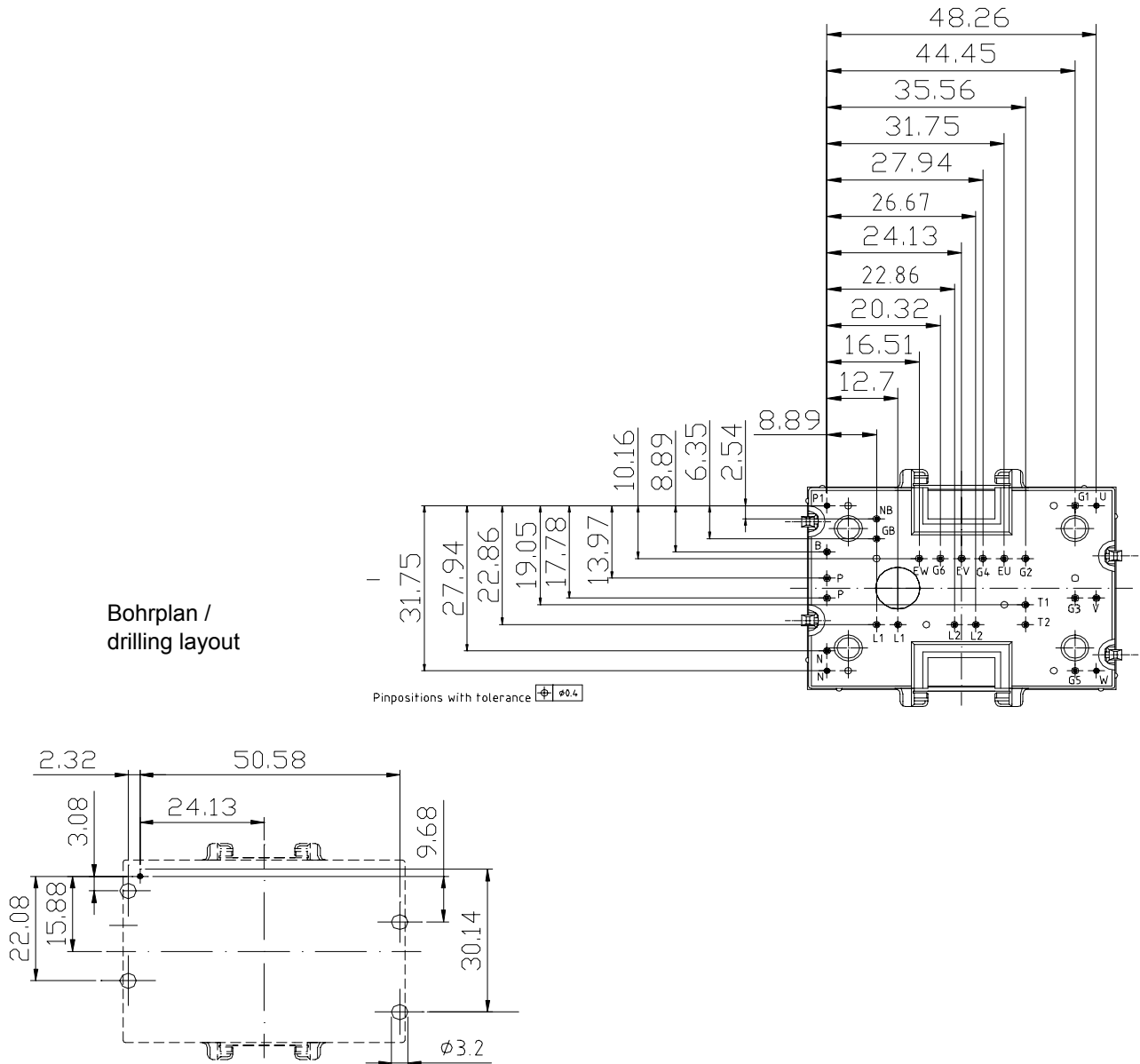
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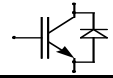
Schaltplan/ circuit diagram



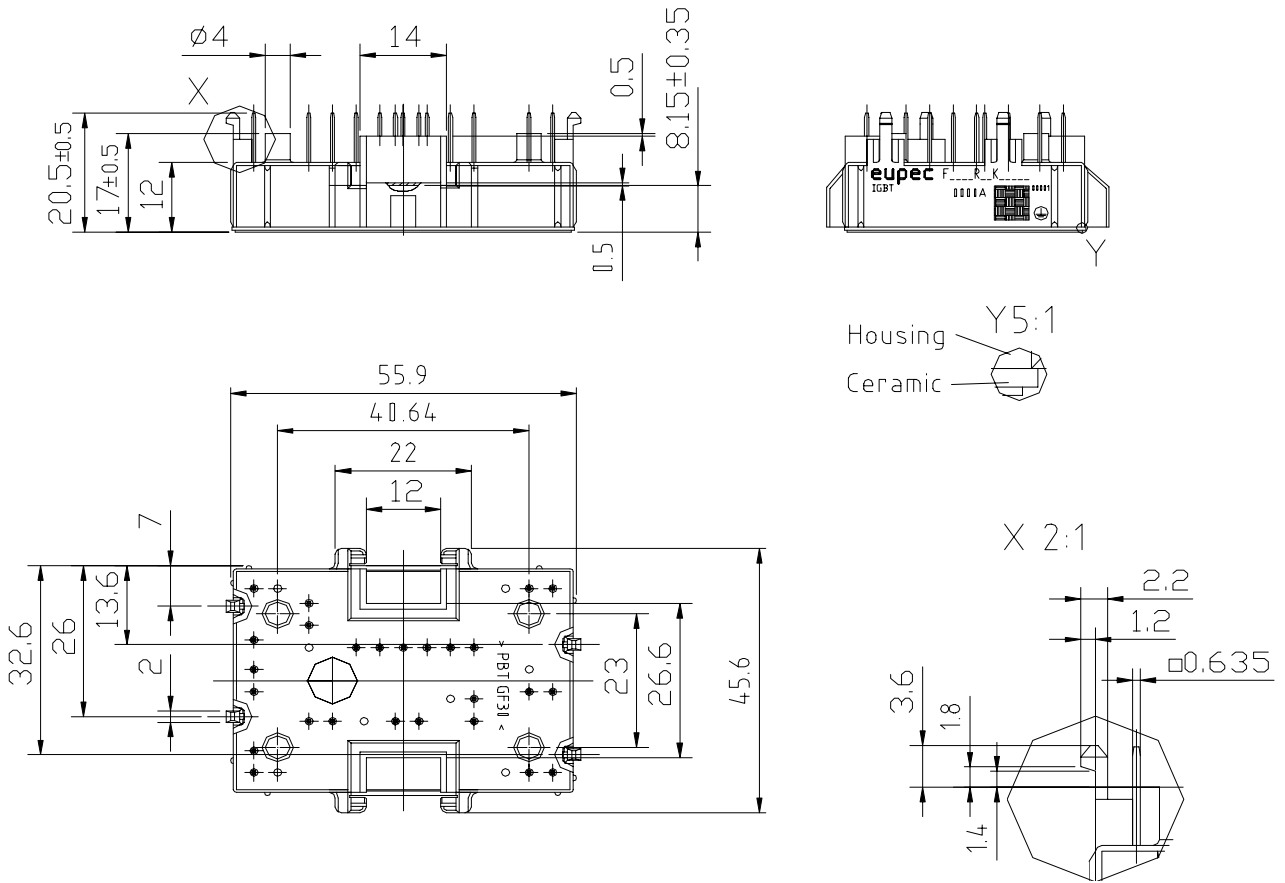
Gehäuseabmessungen/ package outlines

Bohrplan /
drilling layout





Gehäuseabmessungen Forts. / package outlines contd.



Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.

This technical information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical note: